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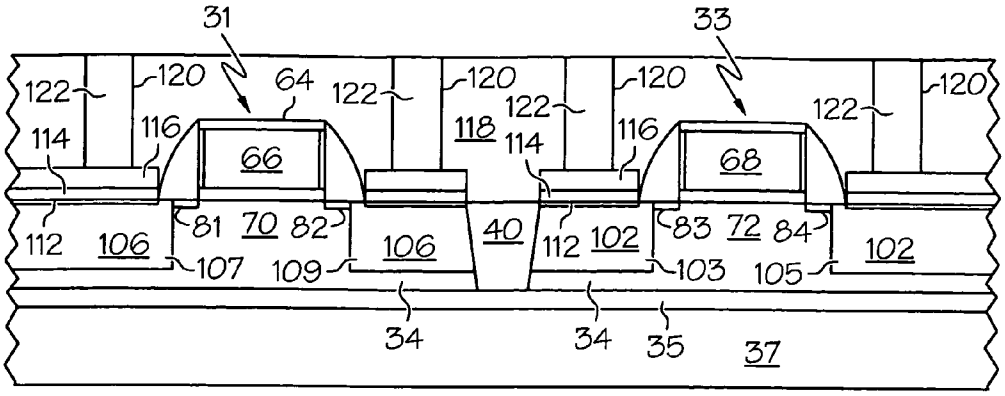


FIG. 10

(57) Abstract: A strain enhanced semiconductor device 30 and methods for its fabrication are provided. One method comprises embedding a strain inducing semiconductor material 102, 106 in the source 103, 107 and drain 105, 109 regions of the device to induce a strain in the device channel 70, 72. Thin metal suicide contacts 112 are formed to the source and drain regions so as not to relieve the induced strain. A layer of conductive material 114, 116 is selectively deposited in contact with the thin metal suicide contacts, and metallized contacts 22 are formed to the conductive material.

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